



PRELIMINARY

**CY62167DV18
MoBL2™**

16M (1024K x 16) Static RAM

Features

- **Very high speed: 55 ns and 70 ns**
- **Voltage range: 1.65V to 1.95V**
- **Ultra-low active power**
 - Typical active current: 1.5 mA @ f = 1 MHz
 - Typical active current: 15 mA @ f = f_{MAX}
- **Ultra-low standby power**
- **Easy memory expansion with CE₁, CE₂ and OE** features
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Packages offered in a 48-ball FBGA**

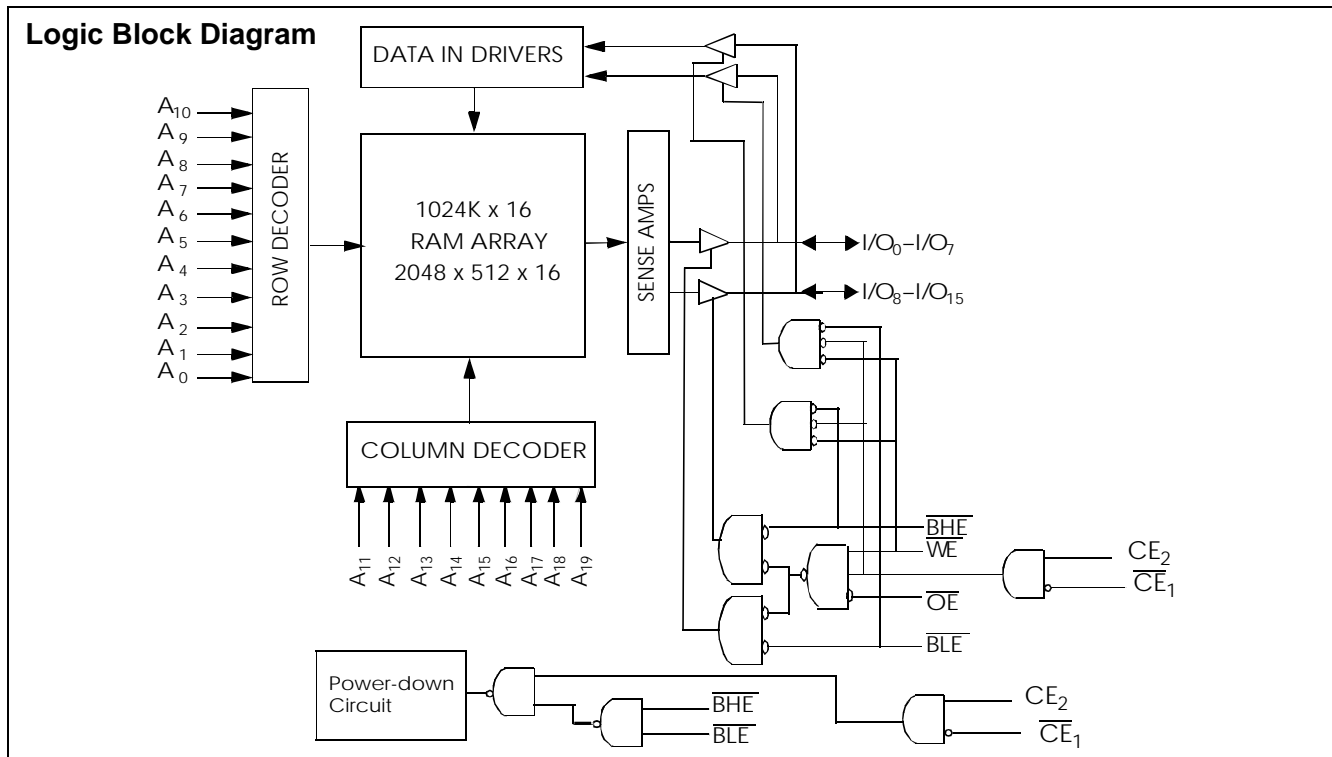
Functional Description^[1]

The CY62167DV18 is a high-performance CMOS static RAM organized as 1024K words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption by 99% when addresses are not

toggling. The device can be put into standby mode reducing power consumption by more than 99% when deselected Chip Enable 1 (\overline{CE}_1) HIGH or Chip Enable 2 (CE_2) LOW or both BHE and BLE are HIGH. The input/output pins (I/O₀ through I/O₁₅) are placed in a high-impedance state when: deselected Chip Enable 1 (\overline{CE}_1) HIGH or Chip Enable 2 (CE_2) LOW, outputs are disabled (\overline{OE} HIGH), both Byte High Enable and Byte Low Enable are disabled (\overline{BHE} , \overline{BLE} HIGH) or during a write operation (Chip Enable 1 (\overline{CE}_1) LOW and Chip Enable 2 (CE_2) HIGH and WE LOW).

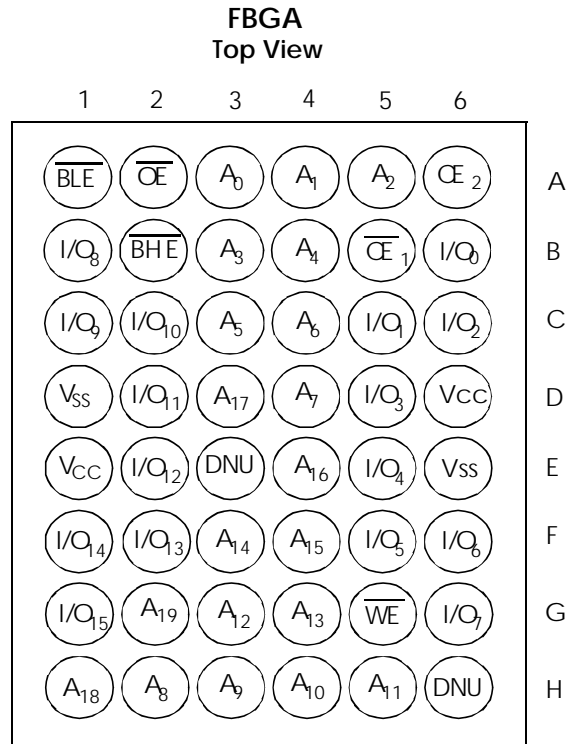
Writing to the device is accomplished by taking Chip Enable 1 (\overline{CE}_1) LOW and Chip Enable 2 (CE_2) HIGH and Write Enable (WE) input LOW. If Byte Low Enable (\overline{BLE}) is LOW, then data pins (A₀ through A₁₉). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address.

Reading from the device is accomplished by taking Chip Enable 1 (\overline{CE}_1) LOW and Chip Enable 2 (CE_2) HIGH and Output Enable (\overline{OE}) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (\overline{BLE}) is LOW, then data from memory will appear on I/O₈ to I/O₁₅. See the truth table at the back of this data sheet for a complete description of read and write modes.



Note:

1. For best practice recommendations, please refer to the Cypress application note "System Design Guidelines" on <http://www.cypress.com>.

Pin Configuration^[2]

Note:

2. DNU pins are to be connected to V_{SS} or left open.



PRELIMINARY

**CY62167DV18
MoBL2™**

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature-65°C to +150°C

Ambient Temperature with Power Applied.....-55°C to +125°C

Supply Voltage to Ground Potential -0.2V to $V_{CCMAX} + 0.2V$

DC Voltage Applied to Outputs in High-Z State^[3]-0.2V to $V_{CC} + 0.2V$

DC Input Voltage^[3] -0.2V to $V_{CC} + 0.2V$

Output Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current..... > 200 mA

Operating Range

| Range | Ambient Temperature (T _A) | V _{CC} ^[4] |
|------------|---------------------------------------|--------------------------------|
| Industrial | -40°C to +85°C | 1.65V to 1.95V |

Product Portfolio

| Product | V _{CC} Range(V) | | | Speed (ns) | Power Dissipation | | | | | |
|---------------|--------------------------|------|------|------------|---------------------------------|------|----------------------|------|--------------------------------|------|
| | | | | | Operating, I _{CC} (mA) | | | | Standby, I _{SB2} (μA) | |
| | Min. | Typ. | Max. | | f = 1 MHz | | f = f _{MAX} | | | |
| | | | | | Typ. | Max. | Typ. | Max. | Typ. | Max. |
| CY62167DV18L | 1.65 | 1.8 | 1.95 | 55 | 1.5 | 5 | 15 | 30 | 2.5 | 30 |
| | | | | 70 | | | 12 | 25 | | |
| CY62167DV18LL | 1.65 | 1.8 | 1.95 | 55 | 1.5 | 5 | 15 | 30 | 2.5 | 20 |
| | | | | 70 | | | 12 | 25 | | |

DC Electrical Characteristics (over the operating range)

| Parameter | Description | Test Conditions | CY62167DV18-55 | | | CY62167DV18-70 | | | Unit |
|------------------|---|---|----------------|------|-----------------------|----------------|------|-----------------------|------|
| | | | Min. | Typ. | Max. | Min. | Typ. | Max. | |
| V _{OH} | Output HIGH Voltage | I _{OH} = -0.1 mA, V _{CC} = 1.65V | 1.4 | | | 1.4 | | | V |
| V _{OL} | Output LOW Voltage | I _{OL} = 0.1 mA, V _{CC} = 1.65V | | | 0.2 | | | 0.2 | V |
| V _{IH} | Input HIGH Voltage | | 1.4 | | V _{CC} + 0.2 | 1.4 | | V _{CC} + 0.2 | V |
| V _{IL} | Input LOW Voltage | | -0.2 | | 0.4 | -0.2 | | 0.4 | V |
| I _{IX} | Input Leakage Current | GND ≤ V _I ≤ V _{CC} | -1 | | +1 | -1 | | +1 | μA |
| I _{OZ} | Output Leakage Current | GND ≤ V _O ≤ V _{CC} , Output Disabled | -1 | | +1 | -1 | | +1 | μA |
| I _{CC} | V _{CC} Operating Supply Current | f = f _{MAX} = 1/t _{RC} , V _{CC} = 1.95V, I _{OUT} = 0mA, CMOS level | | 15 | 30 | | 12 | 25 | mA |
| | | f = 1 MHz | | 1.5 | 5 | | 1.5 | 5 | |
| I _{SB1} | Automatic CE Power-down Current – CMOS Inputs | CE ₁ ≥ V _{CC} - 0.2V, CE ₂ ≤ 0.2V, V _{IN} ≥ V _{CC} - 0.2V, V _{IN} ≤ 0.2V, f = f _{MAX} (Address and Data Only), f = 0 (OE, WE, BHE and BLE) | L | 2.5 | 30 | | 2.5 | 30 | μA |
| | | | LL | 2.5 | 20 | | 2.5 | 20 | |
| I _{SB2} | Automatic CE Power-down Current – CMOS Inputs | CE ₁ ≥ V _{CC} - 0.2V, CE ₂ ≤ 0.2V, V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V, f = 0, V _{CC} = 1.95V | L | 2.5 | 30 | | 2.5 | 30 | μA |
| | | | LL | 2.5 | 20 | | 2.5 | 20 | |

Capacitance^[5]

| Parameter | Description | Test Conditions | Max. | Unit |
|------------------|--------------------|--|------|------|
| C _{IN} | Input Capacitance | TA = 25°C, f = 1 MHz | 6 | pF |
| C _{OUT} | Output Capacitance | V _{CC} = V _{CC(typ)} | 8 | pF |

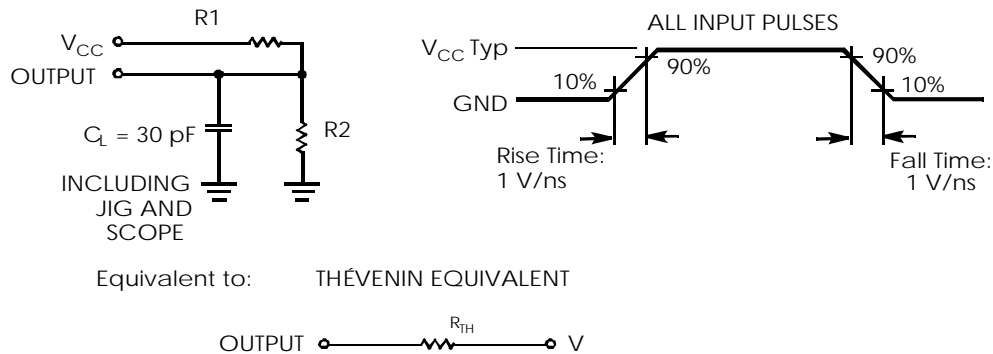
Notes:

- V_{IL(min.)} = -2.0V for pulse durations less than 20 ns.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ)}, T_A = 25°C.
- Tested initially and after any design or process changes that may affect these parameters.

Thermal Resistance

| Parameter | Description | Test Conditions | BGA | Unit |
|---------------|---|--|-----|------|
| θ_{JA} | Thermal Resistance (Junction to Ambient) ^[5] | Still Air, soldered on a 3 x 4.5 inch, two-layer printed circuit board | 55 | C/W |
| θ_{JC} | Thermal Resistance (Junction to Case) ^[5] | | 16 | C/W |

AC Test Loads and Waveforms

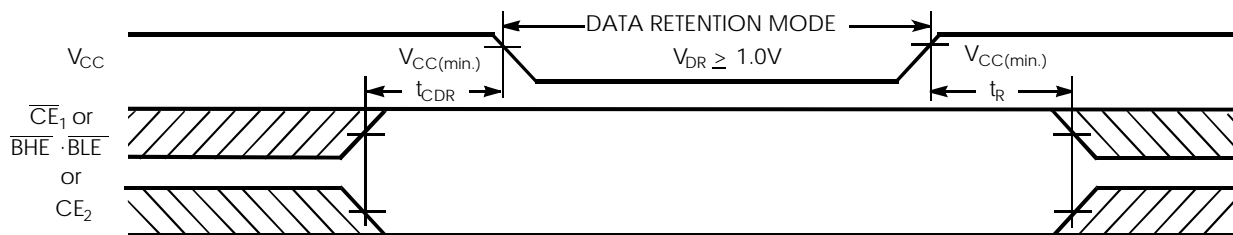


| Parameters | 1.8V | UNIT |
|------------|-------|----------|
| R 1 | 13500 | Ω |
| R 2 | 10800 | Ω |
| R_{TH} | 6000 | Ω |
| V_{TH} | 0.80 | V |

Data Retention Characteristics

| Parameter | Description | Conditions | Min. | Typ. | Max. | Unit |
|-----------------|--------------------------------------|---|----------|------|------|---------|
| V_{DR} | V_{CC} for Data Retention | | 1.0 | | 1.95 | V |
| I_{CCDR} | Data Retention Current | $V_{CC}=1.0V, CE_1 \geq V_{CC} - 0.2V, CE_2 \leq 0.2V, V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$ | L | | 15 | μA |
| | | | LL | | 10 | |
| $t_{CDR}^{[5]}$ | Chip Deselect to Data Retention Time | | 0 | | | ns |
| $t_R^{[6]}$ | Operation Recovery Time | | t_{RC} | | | ns |

Data Retention Waveform^[7]



Notes:

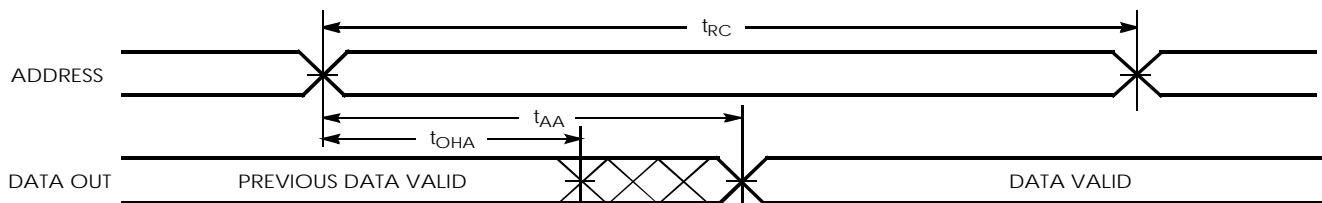
6. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)} > 100 \mu s$ or stable at $V_{CC(min.)} > 100 \mu s$.
7. $\overline{BHE} \cdot \overline{BLE}$ is the AND of both \overline{BHE} and \overline{BLE} . Chip can be deselected by either disabling the chip enable signals or by disabling both \overline{BHE} and \overline{BLE} .

Switching Characteristics (over the operating range)^[8]

| Parameter | Description | CY62167DV18-55 | | CY62167DV18-70 | | Unit |
|-----------------------------------|--|----------------|------|----------------|------|------|
| | | Min. | Max. | Min. | Max. | |
| Read Cycle | | | | | | |
| t _{RC} | Read Cycle Time | 55 | | 70 | | ns |
| t _{AA} | Address to Data Valid | | 55 | | 70 | ns |
| t _{OHA} | Data Hold from Address Change | 10 | | 10 | | ns |
| t _{ACE} | CE ₁ LOW or CE ₂ HIGH to Data Valid | | 55 | | 70 | ns |
| t _{DOE} | OE LOW to Data Valid | | 25 | | 35 | ns |
| t _{LZOE} | OE LOW to Low Z ^[9] | 5 | | 5 | | ns |
| t _{HZOE} | OE HIGH to High Z ^[9, 11] | | 20 | | 25 | ns |
| t _{LZCE} | CE ₁ LOW or CE ₂ HIGH to Low Z ^[9] | 10 | | 10 | | ns |
| t _{HZCE} | CE ₁ HIGH or CE ₂ LOW to High Z ^[9, 11] | | 20 | | 25 | ns |
| t _{PU} | CE ₁ LOW or CE ₂ HIGH to Power-up | 0 | | 0 | | ns |
| t _{PD} | CE ₁ HIGH or CE ₂ LOW to Power-down | | 55 | | 70 | ns |
| t _{DBE} | BLE/BHE LOW to Data Valid | | 55 | | 70 | ns |
| t _{LZBE} ^[10] | BLE/BHE LOW to Low Z ^[9] | 5 | | 5 | | ns |
| t _{HZBE} | BLE/BHE HIGH to High-Z ^[9, 11] | | 20 | | 25 | ns |
| Write Cycle^[12] | | | | | | |
| t _{WC} | Write Cycle Time | 55 | | 70 | | ns |
| t _{SCE} | CE ₁ LOW or CE ₂ HIGH to Write End | 40 | | 60 | | ns |
| t _{AW} | Address Set-up to Write End | 40 | | 60 | | ns |
| t _{HA} | Address Hold from Write End | 0 | | 0 | | ns |
| t _{SA} | Address Set-up to Write Start | 0 | | 0 | | ns |
| t _{PWE} | WE Pulse Width | 40 | | 45 | | ns |
| t _{BW} | BLE/BHE LOW to Write End | 45 | | 60 | | ns |
| t _{SD} | Data Set-up to Write End | 25 | | 30 | | ns |
| t _{HD} | Data Hold from Write End | 0 | | 0 | | ns |
| t _{HZWE} | WE LOW to High Z ^[9, 11] | | 20 | | 25 | ns |
| t _{LZWE} | WE HIGH to Low Z ^[9] | 10 | | 10 | | ns |

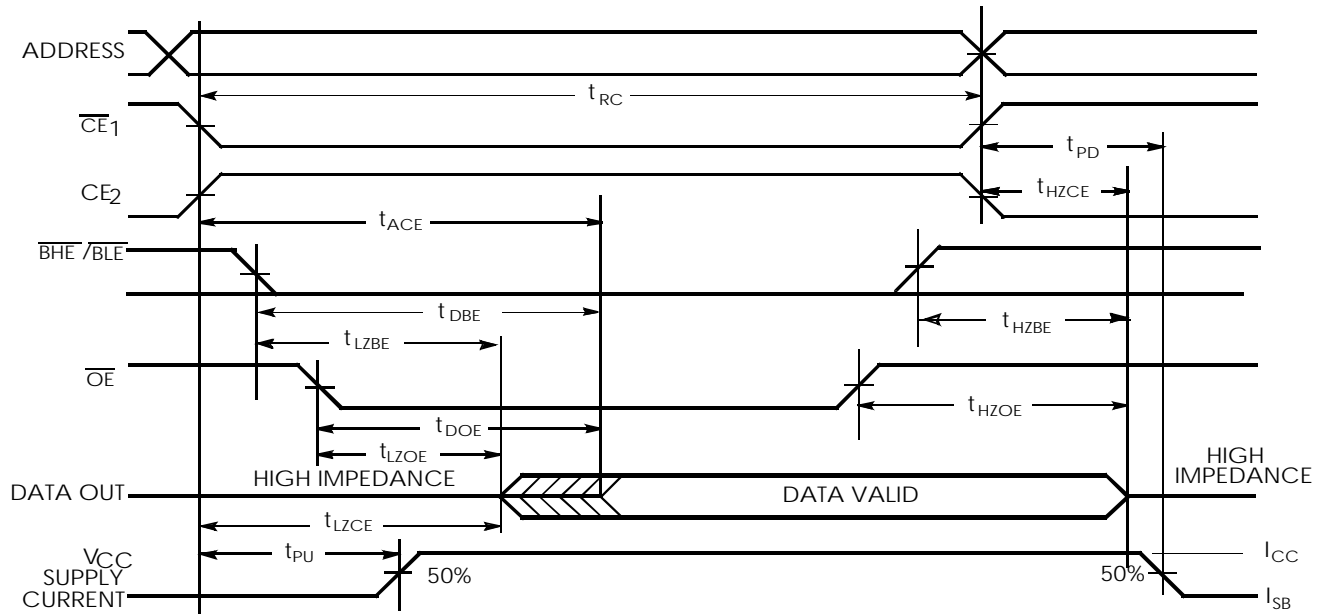
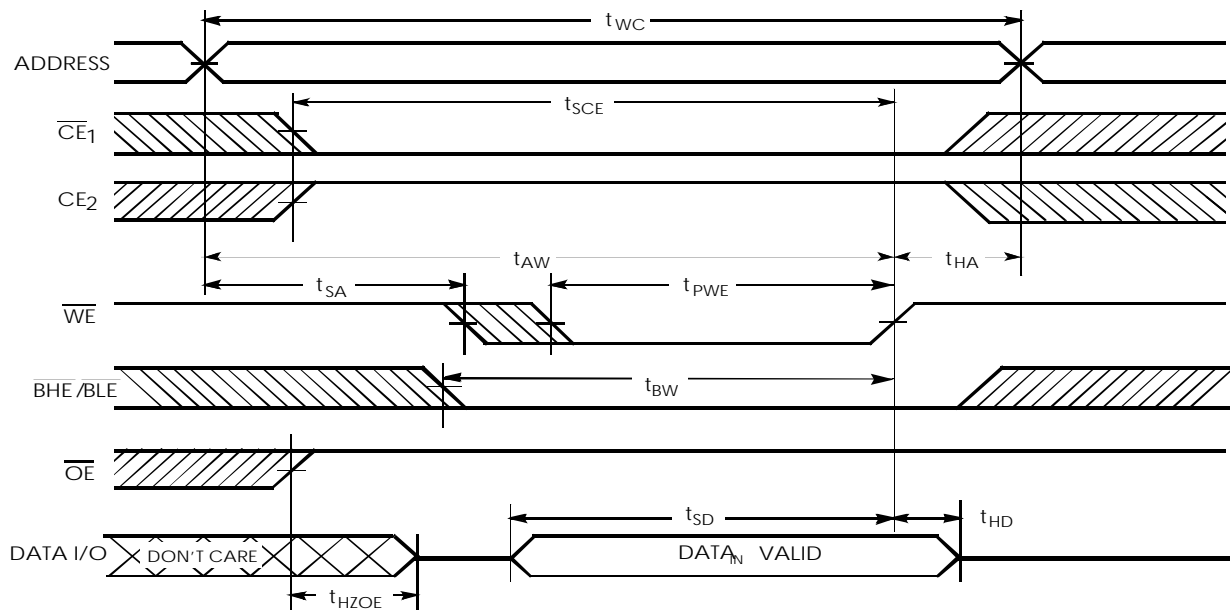
Switching Waveforms

Read Cycle No. 1 (Address Transition Controlled)^[13, 14]

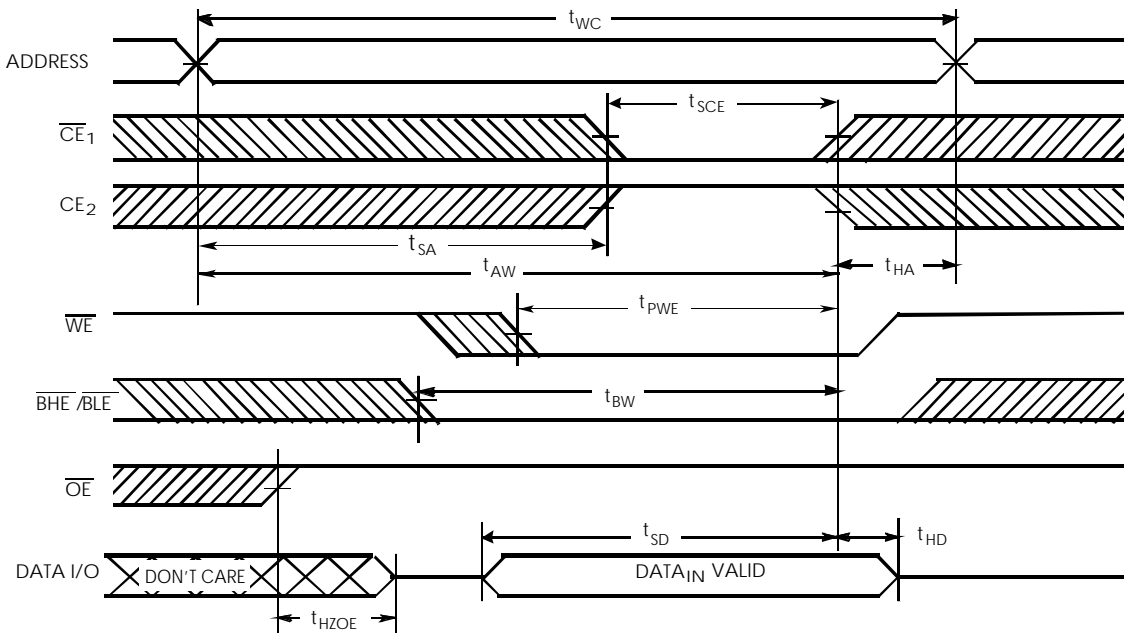
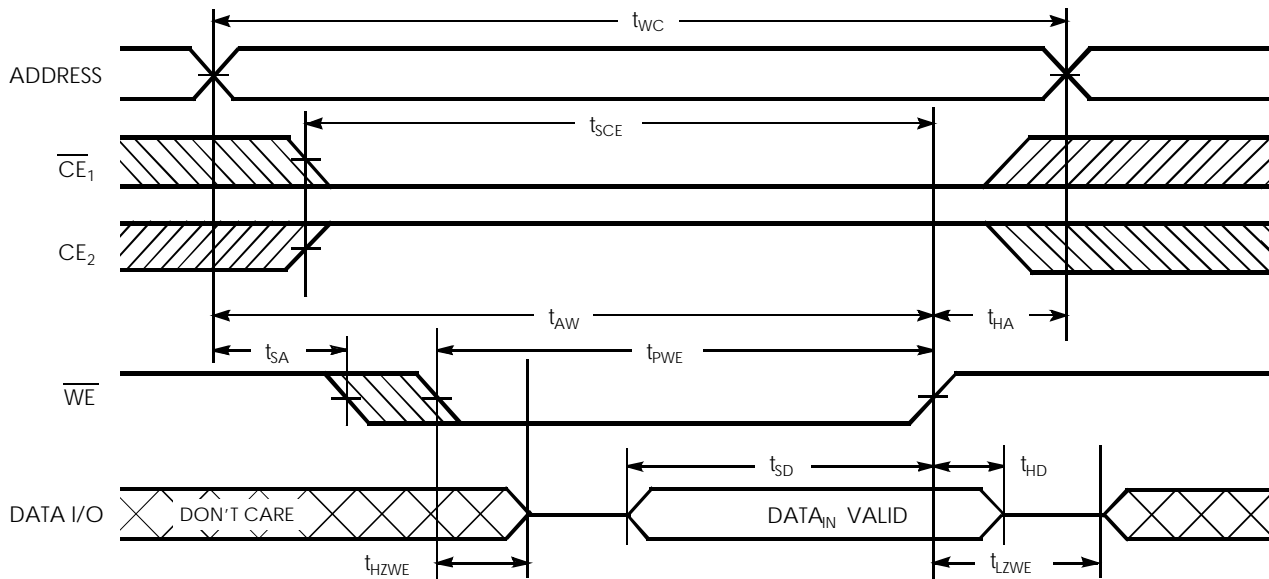


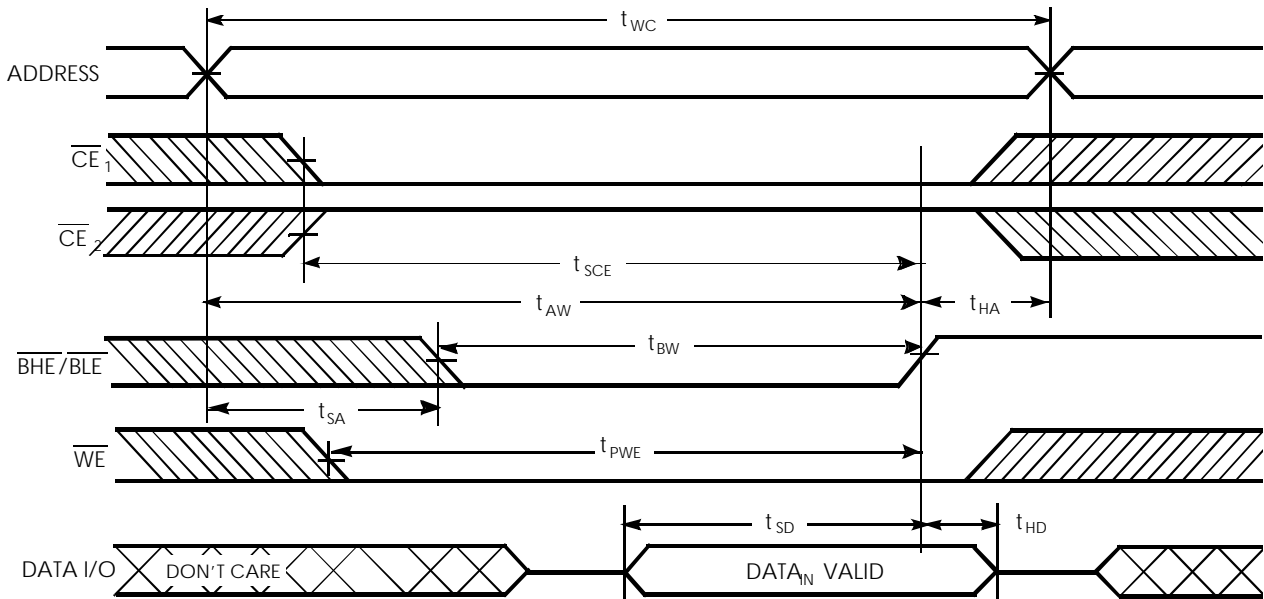
Notes:

8. Test conditions assume signal transition time of 3 ns or less, timing reference levels of $V_{CC(typ.)/2}$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL} .
9. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZBE} is less than t_{LZBE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
10. If both byte enables are toggled together, this value is 10 ns.
11. t_{HZOE} , t_{HZCE} , t_{HZBE} , and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.
12. The internal Write time of the memory is defined by the overlap of WE, $CE_1 = V_{IL}$, BHE and/or BLE = V_{IL} .
13. Device is continuously selected. OE, $CE_1 = V_{IL}$, BHE and/or BLE = V_{IL} , $CE_2 < Def >$
14. WE is HIGH for Read cycle.

Switching Waveforms (continued)
Read Cycle No. 2 ($\overline{\text{OE}}$ Controlled)^[14, 15]

Write Cycle No. 1 ($\overline{\text{WE}}$ Controlled)^[12, 16, 17, 18]

Note:

15. Address valid prior to or coincident with $\overline{\text{CE}}_1$, $\overline{\text{BHE}}$, BLE transition LOW and CE_2 transition HIGH.

Switching Waveforms (continued)
Write Cycle No. 2 (CE<1> or CE<2> Controlled)^[12, 16, 17, 18]

Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW)^[17, 18]


Switching Waveforms (continued)
Write Cycle No. 4 (BHE</>/BLE</> Controlled, OE</> LOW)</>^[17]

Notes:

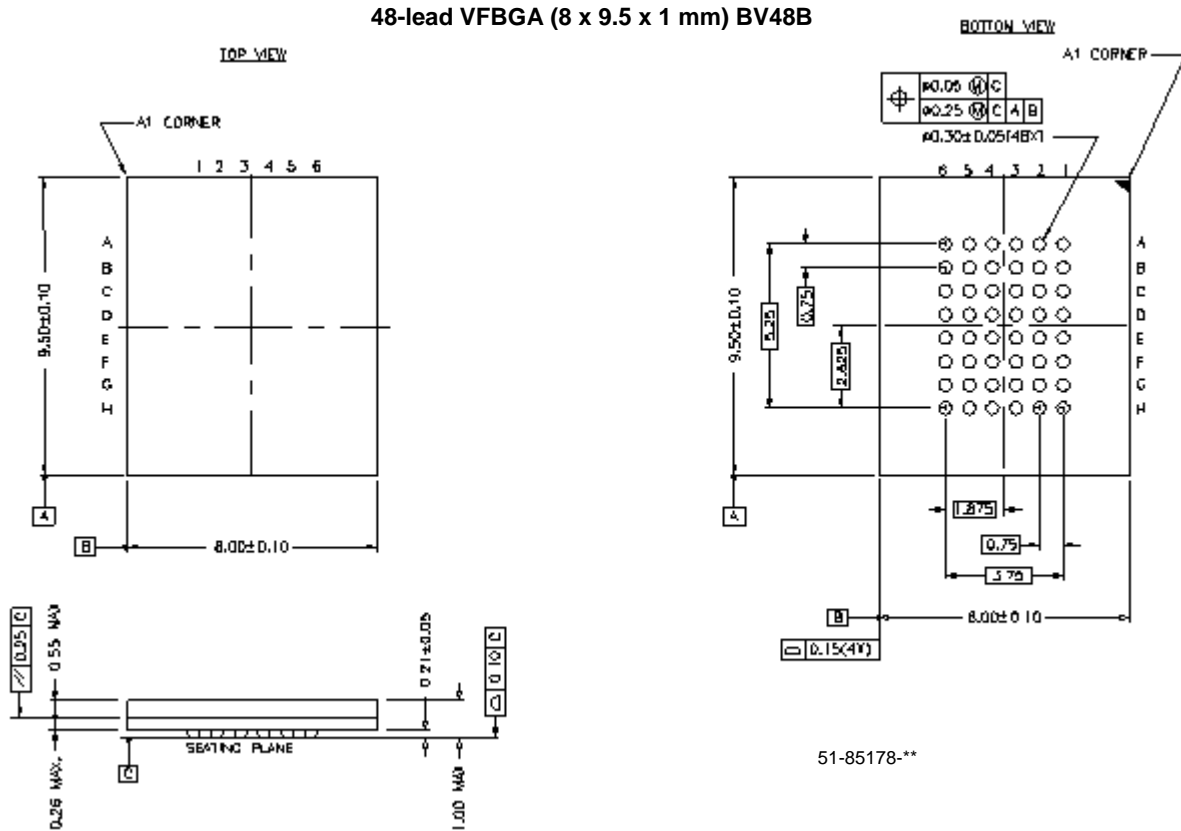
16. Data I/O is high-impedance if $\overline{OE} = V_{IH}$.
17. If \overline{CE}_1 goes HIGH or \overline{CE}_2 goes LOW simultaneously with \overline{WE} HIGH, the output remains in a high-impedance state.
18. During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Truth Table

| \overline{CE}_1 | \overline{CE}_2 | \overline{WE} | \overline{OE} | BHE | BLE | Input / Outputs | Mode | Power |
|-------------------|-------------------|-----------------|-----------------|-----|-----|---|---------------------|---------------------|
| H | X | X | X | X | X | High Z | Deselect/Power-down | Standby(I_{SB}) |
| X | L | X | X | X | X | High Z | Deselect/Power-down | Standby(I_{SB}) |
| X | X | X | X | H | H | High Z | Deselect/Power-down | Standby(I_{SB}) |
| L | H | H | L | L | L | Data Out(I/O0- I/O15) | Read | Active(I_{CO}) |
| L | H | H | L | H | L | Data Out(I/O0- I/O7); High Z (I/O8- I/O15) | Read | Active(I_{CO}) |
| L | H | H | L | L | H | High Z (I/O0- I/O7); Data Out(I/O8- I/O15) | Read | Active(I_{CO}) |
| L | H | H | H | L | H | High Z | Output Disabled | Active(I_{CO}) |
| L | H | H | H | H | L | High Z | Output Disabled | Active(I_{CO}) |
| L | H | H | H | L | L | High Z | Output Disabled | Active(I_{CO}) |
| L | H | L | X | L | L | Data In (I/O0- I/O15) | Write | Active(I_{CO}) |
| L | H | L | X | H | L | Data In (I/O0- I/O7); High Z (I/O8- I/O15) | Write | Active(I_{CO}) |
| L | H | L | X | L | H | High Z (I/O0- I/O7); Data In (I/O8- I/O15) | Write | Active(I_{CO}) |

Ordering Information

| Speed (ns) | Ordering Code | Package Name | Package Type | Operating Range |
|------------|---------------------|--------------|---|-----------------|
| 55 | CY62167DV18L-55**I | TBD | 48-ball Fine Pitch BGA (8.0 x 9.5 x 1.0 mm) | Industrial |
| | CY62167DV18LL-55**I | TBD | 48-ball Fine Pitch BGA (8.0 x 9.5 x 1.0 mm) | |
| 70 | CY62167DV18L-70**I | TBD | 48-ball Fine Pitch BGA (8.0 x 9.5 x 1.0 mm) | Industrial |
| | CY62167DV18LL-70**I | TBD | 48-ball Fine Pitch BGA (8.0 x 9.5 x 1.0 mm) | |

Package Diagram


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Document History Page

| Document Title: CY62167DV18MoBL2™ 16M (1024K x 16) Static RAM Document Number: 38-05326 | | | | |
|--|---------|------------|-----------------|---|
| REV. | ECN NO. | Issue Date | Orig. of Change | Description of Change |
| ** | 118406 | 09/30/02 | GUG | New Data Sheet |
| *A | 123690 | 02/11/03 | DPM | Changed Advance to Preliminary Added package diagram |
| *B | 126554 | 04/25/03 | DPM | Minor Change: Changed sunset owner from DPM to HRT |